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(54) **SOLID-STATE IMAGING DEVICE AND ELECTRONIC APPARATUS**

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(57) **ABSTRACT**

The quantum efficiency can be improved. A solid-state imaging device according to an embodiment includes: a plurality of pixels (**110**) arranged in a matrix, in which each of the pixels includes a first semiconductor layer (**35**), a photoelectric conversion section (PD**1**) disposed on the first semiconductor layer on a side of a first surface, an accumulation electrode (**37**) disposed on the first semiconductor layer close to a side of a second surface on a side opposite to the first surface, a wiring (**61**, **62**, **63**, **64**) extending from the second surface of the first semiconductor layer, a floating diffusion region (FD**1**) connected to the first semiconductor layer via the wiring, and a first gate (**11**) that forms a potential barrier in a charge flow path from the first semiconductor layer to the floating diffusion region via the wiring.